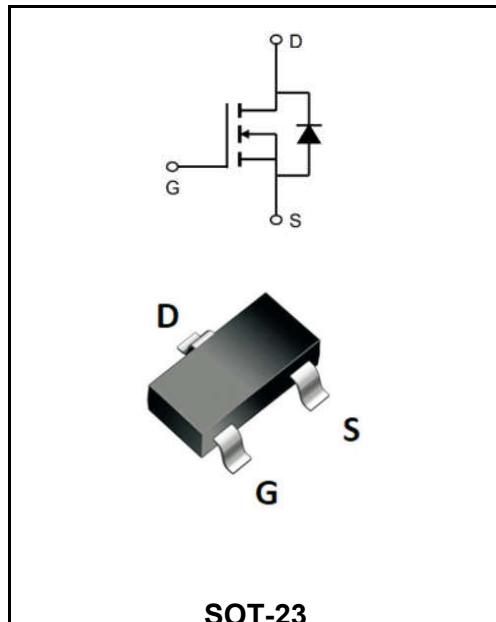


20V N-CHANNEL ENHANCEMENT MODE MOSFET
MAIN CHARACTERISTICS

| | |
|--------------------------------|----------------------|
| I_D | 2.3A |
| V_{DSS} | 20V |
| $R_{DS(on)-typ}(@V_{GS}=4.5V)$ | < 56mΩ (Type: 43 mΩ) |


Application

- Battery protection
- Load switch
- Uninterruptible power supply

| Marking Code | |
|--------------|-------------|
| YFW2300B | 2300./A2SHB |

Maximum Ratings at $T_c=25^\circ\text{C}$ unless otherwise specified

| Characteristics | Symbols | Value | Units |
|--|-----------------|-------------|-------|
| Drain-Source Voltage | V_{DS} | 20 | V |
| Gate - Source Voltage | V_{GS} | ± 12 | V |
| Continuous Drain Current, $V_{GS} @ 4.5V$ @ $T_A=25^\circ\text{C}$ | I_D | 2.3 | A |
| Continuous Drain Current, $V_{GS} @ 4.5V$ @ $T_A=70^\circ\text{C}$ | I_D | 1.8 | A |
| Pulsed Drain Current ^A | I_{DM} | 14 | A |
| Total Power Dissipation ³ @ $T_A=25^\circ\text{C}$ | P_D | 0.7 | W |
| Thermal Resistance Junction-to-Ambient @Steady State | $R_{\theta JA}$ | 178 | °C/W |
| Operating Junction Temperature Range | T_J, T_{STG} | -55 to +150 | °C |

Maximum Ratings at T_c=25°C unless otherwise specified

| Characteristics | Test Condition | Symbols | Min | Typ | Max | Units |
|---------------------------------------|---|---------------------|------|------|------|-------|
| Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250μA | BV _{DSS} | 20 | 21 | - | V |
| Zero Gate Voltage Drain Current | V _{DS} =20V, V _{GS} =0V, T _J =25°C | I _{DSS} | - | - | 1 | μA |
| Gate-Body Leakage Current | V _{GS} =±12V, V _{DS} =0V | I _{GSS} | - | - | ±100 | nA |
| Gate -Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | V _{GS(th)} | 0.52 | 0.66 | 0.9 | V |
| Static Drain-Source On-Resistance | V _{GS} =4.5V, I _D =2.0A | R _{DS(ON)} | - | 43 | 56 | mΩ |
| | V _{GS} =2.5V, I _D =1.5A | | - | 58 | 78 | |
| Input Capacitance | V _{DS} =10V V _{GS} =0V f=1.0MHz | C _{iss} | - | 280 | - | pF |
| Output Capacitance | | C _{oss} | - | 46 | - | |
| Reverse Transfer Capacitance | | C _{rss} | - | 29 | - | |
| Total Gate Charge | V _{GS} =4.5V V _{DS} =10V I _D =3.0A | Q _g | - | 2.9 | - | nC |
| Gate-Source Charge | | Q _{gs} | - | 0.4 | - | |
| Gate-Drain Charge | | Q _{gd} | - | 0.6 | - | |
| Turn-on delay time | V _{GS} =4.5V V _{DD} =10V R _L =1.5Ω R _{GEN} =3Ω | t _{d(on)} | - | 13 | - | ns |
| Turn-on Rise Time | | T _r | - | 54 | - | |
| Turn-Off Delay Time | | t _{d(OFF)} | - | 18 | - | |
| Turn-Off Fall Time | | t _f | - | 11 | - | |
| Maximum Body-Diode Continuous Current | | I _s | - | - | 3.0 | A |
| Diode Forward Voltage | V _{GS} =0V, I _s =3.0A | V _{SD} | - | - | 1.2 | V |

Note:

1、Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.

2、Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

Ratings and Characteristic Curves

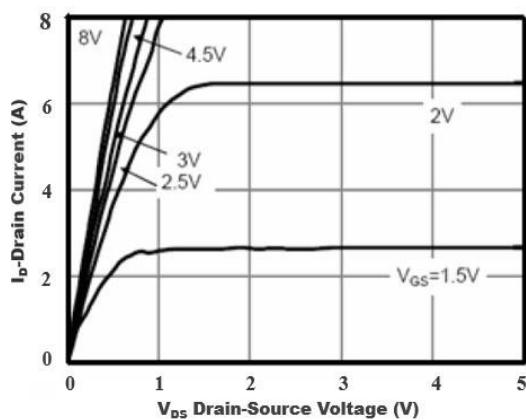


Figure1. Output Characteristics

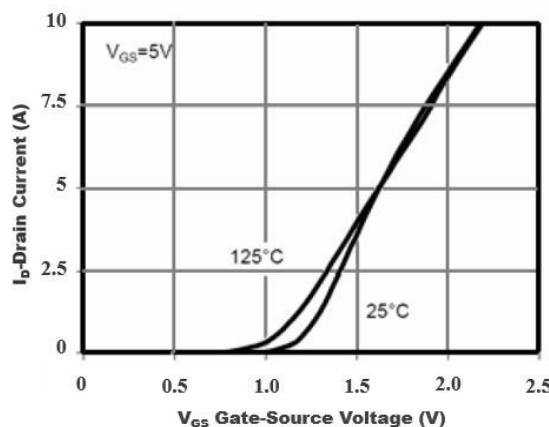


Figure2. Transfer Characteristics

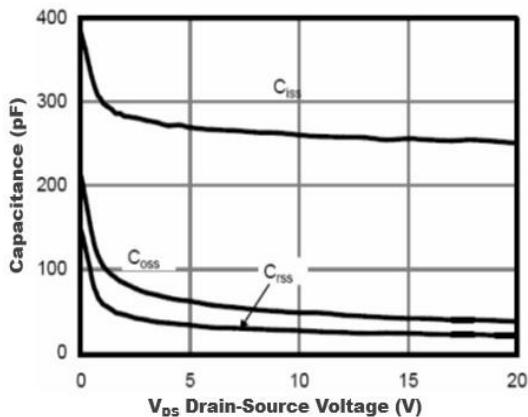


Figure3. Capacitance Characteristics

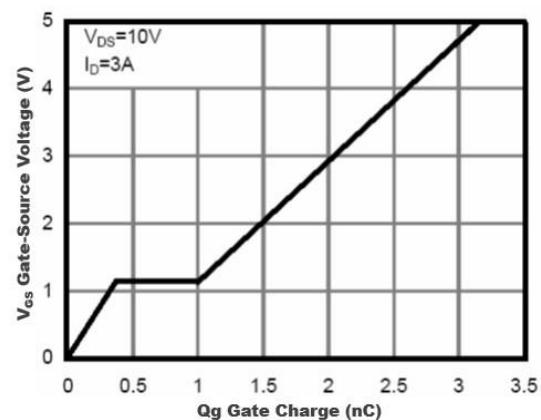


Figure4. Gate Charge

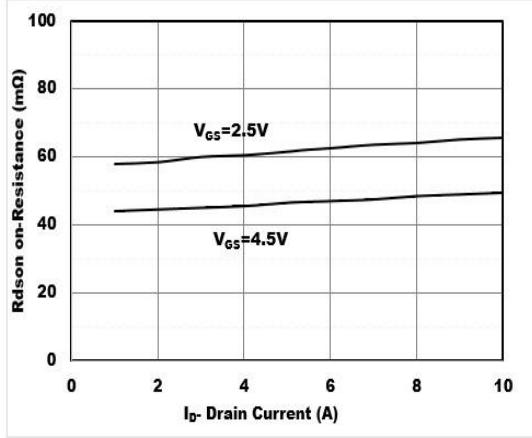


Figure5. Drain-Source on Resistance

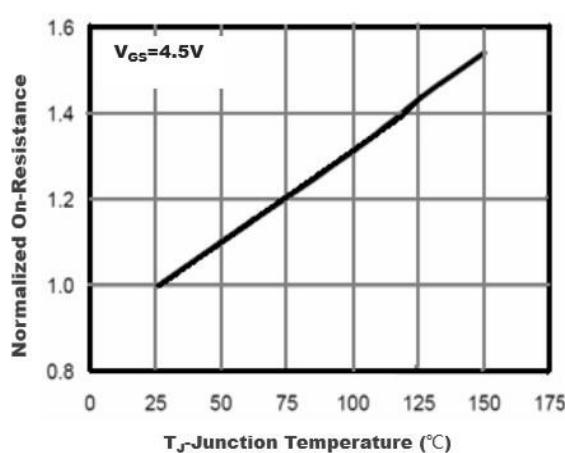


Figure6. Drain-Source on Resistance

Ratings and Characteristic Curves

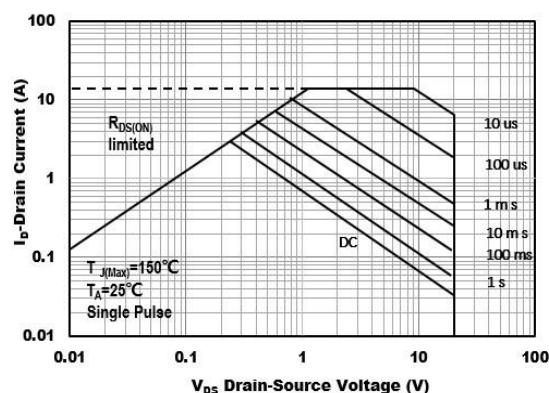


Figure7. Safe Operation Area

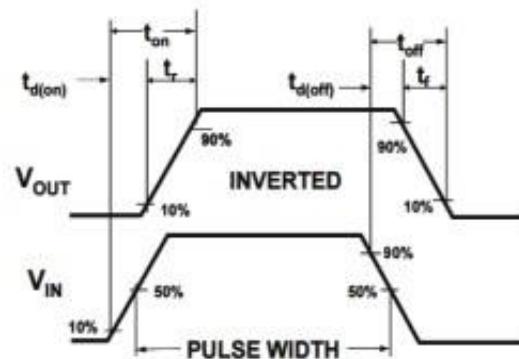


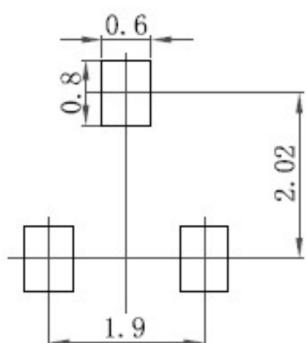
Figure8. Switching wave

Ordering information

| Package | Packing Description | Base Quantity | Packing Quantity |
|---------|---------------------|---------------|-------------------------------|
| SOT-23 | Tape/Reel,7"reel | 3000pcs/Reel | 24000PCS/Box 120000PCS/Carton |

Package Dimensions
SOT-23

| Dim. | Millimeter (mm) | | mil | |
|------|--------------------|------|------|------|
| | Min. | Max. | Min. | Max. |
| A | 0.9 | 1.15 | 35 | 45 |
| A1 | 0.1 | | 3.9 | |
| bp | 0.38 | 0.48 | 15 | 19 |
| C | 0.09 | 0.15 | 3.54 | 5.9 |
| D | 2.8 | 3.0 | 110 | 118 |
| E | 1.2 | 1.4 | 47 | 55 |
| E | 1.9 | | 75 | |
| E1 | 0.95 | | 37 | |
| HE | 2.1 | 2.55 | 83 | 100 |
| Lp | 0.15 | 0.45 | 5.9 | 18 |
| Q | 0.45 | 0.55 | 18 | 22 |
| v | 0.2 | | 7.9 | |
| W | 0.1 | | 4 | |

The recommended mounting pad size


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